	. 330	Search Text	DB	Time stamp
		(tft or thin near film near transistor or	USPAT;	2004/01/21 11:33
		transistor near3 soi) same (single adj	US-PGPUB;	
		crystal or single adj crystalline or single	EPO; JPO;	
		adj grain or monocrystal or monocrystalline	DERWENT;	
		or single adj grained or one adj grain or	IBM_TDB	
		mono adj crystal or mono adj crystalline)		
		same (nickel or ni or cobalt or co or		
		palladium or pd or aluminum or al or		
		titanium or ti or transition adj metal)		
	169	(tft or thin near film near transistor or	USPAT;	2004/01/21 11:34
		transistor near3 soi) same (single adj	US-PGPUB;	
		crystal or single adj crystalline or single	EPO; JPO;	
1		adj grain or monocrystal or monocrystalline	DERWENT;	
.		or single adj grained or one adj grain or	IBM TDB	
		mono adj crystal or mono adj crystalline)	_	
1		same (nickel or ni or cobalt or co or		
		palladium or pd or aluminum or al or		
		titanium or ti or transition adj metal) same		
		(insulator or insulating or oxide or nitride		
1		or sin or sio)		
	27	- '	USPAT;	2004/01/21 11:35
		transistor near3 soi) same (single adj	US-PGPUB;	2004/01/21 11:35
		crystal or single adj crystalline or single		
		adj grain or monocrystal or monocrystalline	EPO; JPO;	
		or single adj grained or one adj grain or	DERWENT;	
ľ		mono adj crystal or mono adj crystalline)	IBM_TDB	
		none adj crystal of mone adj crystalline)		
		near10 (nickel or ni or cobalt or co or		
		palladium or pd or aluminum or al or		
,		titanium or ti or transition adj metal) same		
	•	(insulator or insulating or oxide or nitride		
	_	or sin or sio)		
	6	(tft or thin near film near transistor or	USPAT;	2004/01/21 11:37
		transistor near3 soi) same (single adj	US-PGPUB;	
		crystal or single adj crystalline or single	EPO; JPO;	1
		adj grain or monocrystal or monocrystalline	DERWENT;	1
		or single adj grained or one adj grain or	IBM TDB	
		mono adj crystal or mono adj crystalline)	_	
		near10 (nickel or ni or cobalt or co or		
		palladium or pd or aluminum or al or		
		titanium or ti or transition adj metal)		
		near10 (doped or doping or diffused or		
		diffusing or diffusion or implant or		
		implanting or dopant or donor or impurity or]
		impurities)		
1	257	(single adj crystal or single adj	USPAT;	2004/01/21 11:39
		crystalline or single adj grain or	US-PGPUB;	
1		monocrystal or monocrystalline or single adj	EPO; JPO;	
1		grained or one adj grain or mono adj crystal		
Į.		or mono adj crystalline) near20 (nickel or	DERWENT;	
		ni or cobalt or co or palladium or pd or	IBM_TDB	
		aluminum or al or titanium or ti or		
-		transition adj metal) near10 (doped or		
		doning or diffused on diffusion and also		
		doping or diffused or diffusing or diffusion		
		or implant or implanting or dopant or donor		
1	1	or impurity or impurities) near10 (amorphous		
		or polysilicon or polycrystalline or poly		
		adj crystalline or a-si or alpha adj si)		
	194	(single adj crystal or single adj	USPAT;	2004/01/21 11:50
	1	crystalline or single adj grain or	US-PGPUB;	
	İ	monocrystal or monocrystalline or single adj	EPO; JPO;	
	1	grained or one adj grain or mono adj crystal	DERWENT;	
		or mono adj crystalline) near15 (nickel or	IBM TDB	
		ni or cobalt or co or palladium or pd or		
		- Passacian of pa Of	1	l .
		aluminum or al or titanium or ti or		
		aluminum or al or titanium or ti or		
		aluminum or al or titanium or ti or transition adj metal) near5 (doped or doping		
		aluminum or al or titanium or ti or transition adj metal) near5 (doped or doping or diffused or diffusing or diffusion or		
		aluminum or al or titanium or ti or transition adj metal) near5 (doped or doping or diffused or diffusing or diffusion or implant or implanting or dopant or donor or		
		aluminum or al or titanium or ti or transition adj metal) near5 (doped or doping or diffused or diffusing or diffusion or		

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Crystalline or single adj grain or monocrystal or	10	52	'J or bringic au		2004/01/21 13:03
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			monocrystal or monocrystalline or single adj		
ni or cobalt or co or palladium or pd or aluminum or al or titanium or al or depote or diffusion or implant or implanting or depart or demot or polystilicon completes means (amorphous or polystilicon completes) means (amorphous or crystallium or al-or or alpha adj all lames (inmulator or insulating or sio or sin or oxide or nitride) 10			grained or one adj grain or mono adj crystal		
aluminum or al or titanium or ti or transition add metal) nears (doped or doping or diffused or diffusing or diffused or diffusing or diffused or diffusing or diffusing or diffused or diffusing or diffusion or impurity or impurities) nears (amorphous or perystilion or polyenytealline or poly add or control or oxide or nitride or insulator or insulating or sin or oxide or nitride or monocrystalline or single add; crystallite or single add; crystallite or single add; grained or one add grain or monocrystal or monocrystalline or single add; grained or one add grain or mono add crystalline or single add; grained or one add grain or mono add crystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or one add grain or monocrystalline or single add; grained or nickel or in or titanium or ti or palladium or pd or cobalt or co or aluminum or all ("5147826" "5275851" "6077731" USPAT USPAT 2004/01/21 13:08 13 588857.pn. 56162657" 780.77731" USPAT 2004/01/21 13:08 2004/01/21 13:18 2004/01/21 13:52 USPAT 2004/01/21 13:53 USPAT 2004/0			ni or dobalt or do or mallading and	TRW_TDB	
transition adj metal) nears (doped or doping or diffused or impurity or impurities) impu			aluminum or all or titanium or pd or		
or diffused or diffusion or implant or implanting or dopant or donor or impurity or impurities) near's (amorphous or polysilicon or polycrystalline or poly adj crystalline or poly adj crystalline or or or insulator or concernation or monoad or crystalline or or adj grain or monoad or crystalline or or or drain) 12			transition add metall nears (doned or doning		
implant or implanting or dopant or donor or impurity o			or diffused or diffusing or diffusion or		
impurity or impurities) near5 (amorphous or polysilicon or polycrystalline or poly adj crystalline or polycrystalline or polycrystalline or polycrystalline or polycrystalline or polycrystalline or sin or oxide or nitride) (for cthin near film near transistor) and (single adj crystalline or single adj crystalline or single adj grain or single adj grain or mono adj crystall or monocrystalline or single adj grain or monocrystalline or single adj grain or monocrystall or monocrystalline or single adj grain or mono adj crystall or mono adj crystalline or single adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or all (single adj crystalline) near5 (channel or source or drain) near15 (transition adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or all (single adj crystalline) near5 (channel or source or drain) near5 (transition adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or all (single adj crystalline) near5 (channel or source or drain) near5 (transition adj metal or nickel or ni or titanium or ti or source or drain) near5 (channel or source or drain)			implant or implanting or donant or donor or		
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Crystalline or a-si or alpha add si) same (insulator or insulating or sio or sin or oxide or nitride) 752 (tfo or thin near film near transistor) and (single adj crystalline or single adj grained or one adj grain or monocrystall or monocrystalline or single adj crystalline or single adj crystalline or single adj crystalline or single adj grained or one adj grain or monocrystall or monocrystalline or single adj crystalline or single adj grain or monocrystalline or single adj grain or monocrystall or monocrystalline or single adj grain or mono adj crystall or monocrystalline or single adj grain or mono adj crystalline or single adj grains) same (aluminum adj film adj transistor) and (single adj crystals4 or single adj grains3) same (aluminum ad cobalt by specific specifi			polysilicon or polycrystalline or poly adi		
11 752 Oxide or nitride) (tfo or thin mear film near transistor) and (single adj crystal or single adj grain or monocrystal or monocrystal or monocrystal or monocrystal ine or single adj crystal or monocrystal or monocrystal ine or single adj crystal or monocrystal or monocrystal ine or monocrystal ine or monocrystal or monocrystal ine or single adj grain or mono adj crystal or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or monocrystal or monocrystal ine or single adj grain or mono adj crystal or monocrystal or monocrystal ine or single adj grain or mono adj crystal or monocrystal or monocrystal or monocrystal or monocrystal or monocrystal or single adj grain or mono adj crystal or single adj grains) 100			crystalline or a-si or alpha adj si) same		
152			(insulator or insulating or sio or sin or		
(single adj crystal or single adj crystal) Crystalline or single adj grain or monocrystal or monocrystal line or single adj grain or mono adj crystal or monocrystal line or single adj grained or one adj grain or mono adj crystal or mono adj crystal or mono adj crystal or mono adj crystal ine or single adj (single adj crystal or single adj crystal or single adj (single adj crystal or single adj crystal or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj grain or mono adj crystal ine or single adj cry	1,,	550			
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monocrystal or monocrystalline or single adj grained or one adj grain or mono adj crystal or mono crystalline or single adj grained or one adj grain or mono adj crystal or mono adj cry	!		(single adj crystal or single adj		
12 11 (tft or thin adj film adj crystal or mono adj crystaline) near5 (channel or source or drain) (tft or thin adj film adj crystaline) near5 (channel or source or drain) (tft or thin adj film adj crystalline) near5 (channel or monocrystal or monocrystalline or single adj grained or one adj grystalline) near5 (channel or source or drain) near15 (transitor) and (single adj or monocrystalline) near5 (channel or source or drain) near15 (transition adj palladium or pd or cobalt or co or aluminum or al) palladium or pd or cobalt or co or aluminum or al) USPAT USPA			monographal or monographalling or simple		
12 11 (tft or thin near film near transistor) and (tsingle adj crystalline or single adj crystalline or single adj crystalline or single adj graine or monocaystal or monocaystalline or single adj grained or one adj crystalline) near's (channel or source or drain) nearl's (transition adj metal or nickel or in or titanium or ti or palladium or pd or cobalt or co or aluminum or al) USPAT US-DPUB: EDO; JPO; DERMEND; IBM_TDB USPAT US			grained or one adi grain or mono adi granal	· ·	
12 11 (tfo or thin near film near transistor) and (single adj crystal) or single adj grained or monocrystal or monocrystalline or single adj grained or one adj grystalline) near5 (channel or source or drain) near15 (transistor) and or mono adj crystalline) near5 (channel or source or drain) near15 (transistor) adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or al) 13 5 ("5147826" "5275851" "6077731" USPAT ("5147826" "5275851" "6077731" USPAT ("5147826" "5275851" "6077731" USPAT ("5147826" "5275851" "6077731" USPAT ("5147826" "6162667" PN. 15 ("5147826" "5275851" "6077731" USPAT ("5147826" "6458637").PN. 16 13 588657.pn. 5744822.pn. 5555544.pn. USPAT; US-PGPUB; EPO, JPO; DERMENT; IBM TDB (USPAT; USPAT; USPAT			or mono adi crystalline) nears (channol or	TRM_IDB	
11			source or drain)		
(single adj crystal or single adj crystal) Crystalline or single adj grain or crystal or monocrystal or mono adj crystalline) near5 (channel or source or drain) near15 (transition adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or al) ("5147826" "5275851" "6077731" USPAT USPAT 2004/01/21 13:08 ("5147826" "5275851" "6077731" USPAT 2004/01/21 13:20 "6084247" "61626667" PN. "6228693" "6228693" "6346437" "6462667" PN. TOPAT USPAT 2004/01/21 13:20 "6346437" "6458673" PN. 5888857.pn. 5744822.pn. 5595944.pn. USPAT	12	11	(tft or thin near film near transistor) and	USPAT:	2004/01/21 13.29
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monocrystal or monocrystalline or single adj grained or one adj grained or mono adj crystal or single adj grains] same (aluminum adj titanium ti nickel nin palladium pd cobalt			crystalline or single adj grain or	1	
or mono adj crystalline) near5 (channel or source or drain) near15 (transition adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or al) 13 5 ["5147826" "5275851" "6077731" USPAT 2004/01/21 13:08 "6084247" "6162667").PN. 14 7 6162667.URPN. 15 8 ["5147826" "5275851" "6077731" USPAT 2004/01/21 13:20 "6084247" "6162667" PN. 16 13 588857.pn. 5744822.pn. 5955944.pn. USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWEN			monocrystal or monocrystalline or single adj	DERWENT;	
Source or drain) nearls (transition adj metal or nickel or ni or titanium or ti or palladium or pd or cobalt or co or aluminum or al) 13 5 ("5147826" "5275851" "6077731" USPAT 2004/01/21 13:08 ("6084247" "6162667").PN. USPAT 2004/01/21 13:18 USPAT 2004/01/21 13:18 USPAT USPAT 2004/01/21 13:20 USPAT USPA			grained or one adj grain or mono adj crystal	IBM_TDB	
metal or nickel or ni or titanium or ti or palladium pa		İ	or mono adj crystalline) near5 (channel or		
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13 5 "5275851" "6077731" USPAT 2004/01/21 13:08 14 7 6162667 URPN. USPAT 2004/01/21 13:08 2004/01/21 13:18 USPAT 2004/01/21 13:20 2004/01/21		1	palladium or pd or cobalt or co or aluminum		
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DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DEPO; JPO; DERWENT;					
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single adj grain\$3) EPO; JPO; DERWENT; IBM_TDB 257/347.ccls. and (tft or thin adj film adj USPAT; transistor) and (single adj crystal\$4 or US-PGPUB; single adj grain\$3) same (aluminum al EPO; JPO; titanium ti nickel ni palladium pd cobalt DERWENT;	20	249	transistor) and (simple and adj		2004/01/21 13:53
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single adj grain\$3) same (aluminum al EPO; JPO; titanium ti nickel ni palladium pd cobalt DERWENT;			transistor) and (single adj crystals4 or		2004/01/21 13:58
titanium ti nickel ni palladium pd cobalt DERWENT;	ľ		single adj grain\$3) same (aluminum al	-	
L CO) IBM TDB			titanium ti nickel ni palladium pd cobalt		
			co)		

22	61	257/66.ccls. and (tft or thin adj film adj	USPAT;	2004/01/21 14:03
		transistor) and (single adj crystal\$4 or	US-PGPUB;	
		single adj grain\$3) same (aluminum al	EPO; JPO;	
		titanium ti nickel ni palladium pd cobalt	DERWENT;	
		co)	IBM TDB	
23	760		USPAT;	2004/01/21 14:05
		(recrystallize or recrystallized or	US-PGPUB;	
		recrystallization or crystallize or	EPO; JPO;	
		crystallized or crystallization or	DERWENT;	
		recrystallizing or crystallizing) near5	IBM TDB	
		(amorphous near2 silicon or alpha near si or	_	
		asi) near8 (nickel ni cobalt co palladium pd		
		aluminum al titanium ti transition adj		
		metal)		
24	192	, the second control of the control	USPAT;	2004/01/21 14:06
		(recrystallize or recrystallized or	US-PGPUB;	
		recrystallization or crystallize or	EPO; JPO;	
	•	crystallized or crystallization or	DERWENT;	
		recrystallizing or crystallizing) near3	IBM TDB	
		(amorphous near2 silicon or alpha near si or	_	
		asi) near5 (nickel ni cobalt co palladium pd		
	1	aluminum al titanium ti transition adj		
		metal) hear10 (heat or anneal or heating or		
		annealing or heated or annealed)		
25	20	(tft or thin adj film adj transistor) and	USPAT;	2004/01/21 14:06
		(recrystallize or recrystallized or	US-PGPUB;	,
		recrystallization or crystallize or	EPO; JPO;	
	'	crystallized or crystallization or	DERWENT;	
		recrystallizing or crystallizing) near3	IBM TDB	
		(amorphous near2 silicon or alpha near si or	_	
		asi) near5 (nickel ni cobalt co palladium pd		
		aluminum al titanium ti transition adj		
		metal) near15 (oxide or nitride or insulator		
		or insulating or dielectric or sin or sio)		